

3 A LOW Vf Schottky Barrier Rectifier

DESCRIPTION

In Microsemi's new Powermite3[®] SMT package, these high efficiency Schottky rectifiers offer the power handing capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies.

In addition to its size advantages, Powermite[®] package features include a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly, and a unique locking tab acts as an integral heat sink. Its innovative design makes this device ideal for use with

automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

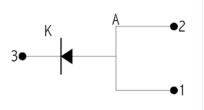
	ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)									
	Rating	Unit								
	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	orking Peak Reverse Voltage V _{RWM} 40								
	RMS Reverse Voltage	V _{R (RMS)}	28	V						
	Average Rectified Output Current	Ι _ο	3	А						
	Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load @ T _c =100 °C	I _{FSM}	50	А						
	Storage Temperature	T _{STG}	-55 to +150 °C							
	Junction Temperature T _J -55 to +125									
	THERMAL CHARACTERISTICS (UNLESS OTHERWISE SPECIFIED) Thermal Resistance									
	Junction-to Case (Bottom)	R _{θJC} (*	1) 3.2	°C/Watt						
			1	I						

KEY FEATURES

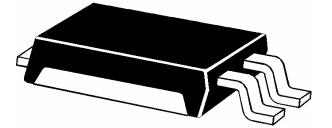
- High power surface mount package.
- Guard Ring die construction for transient protection.
- Internal heat sink locking tabs
- Low forward voltage.
- Full metallic bottom eliminates
 flux entrapment
- Compatible with automatic insertion equipment
- Low profile-maximum height of 1mm supplied in 16 mm tape reel- 5000 units/ 13" reel.

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits.
- Reduces reverse recovery loss due to low I_{RM}.
- Small foot print 190 X 270 mils (1:1 Actual size) See mounting pad details on pg 3



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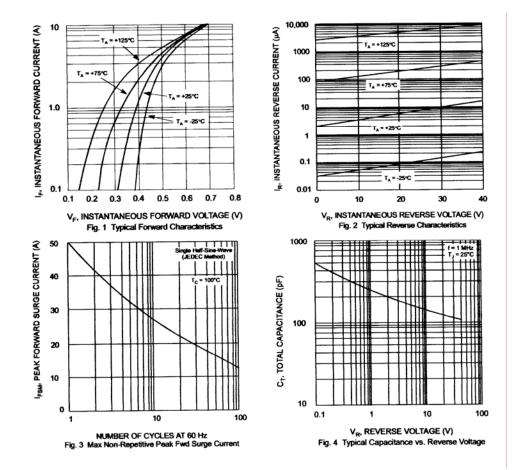




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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)									
Parameter	Symbol	Conditions	Min	Тур.	Max	Units			
Forward Voltage (Note 1)		L = 2.0 T = 25.9C		0.46	0.50				
Torward Voltage (Note T)		I _F = 3 A , T _j =25 °C I _F = 3 A , T _j =125 °C		0.40	0.30	.,			
	V _F	$I_F = 6 \text{ A}$, $T_j = 25 \text{ °C}$		0.57	0.61	V			
		I _F = 6 A , T _j =125 °C		0.54	0.58				
Reverse Break Down Voltage (Note 1)	V_{BR}	I _R = 0.5 mA	40			V			
Reverse Current (Note1)		$V_{R} = 40V, T_{j} = 25 \text{ °C}$		15	500	uA			
	I _R	$V_{R} = 40V, T_{j} = 100 \ ^{\circ}C$		10	20	mA			
Capacitance	Ст	$V_{R} = 4 V; f = 1 MH_{Z}$		180		pF			

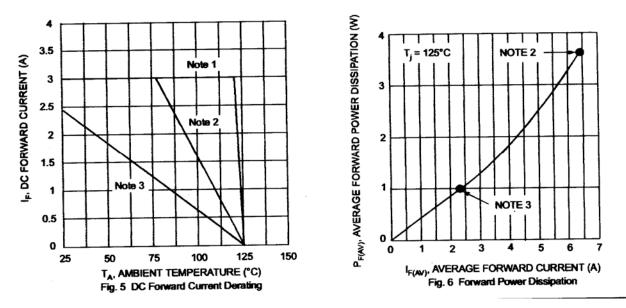
Note: 1 Short duration test pulse used to minimize self - heating effect.



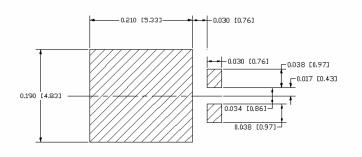
UPS340



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- Notes: 1. $T_A = T_{SOLDERING POINT}$, $R_{\Theta JS} = 3.2^{\circ} \text{ C/W}$ $R_{\Theta SA} = 0^{\circ} \text{ C/W}$. 2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R_{OJA} in range of 20-40° C/W.
 - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout $R_{\Theta JA}$ in range of 65° C/W. See mounting pad below.

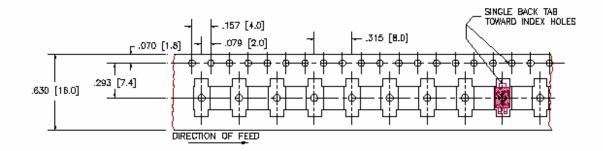




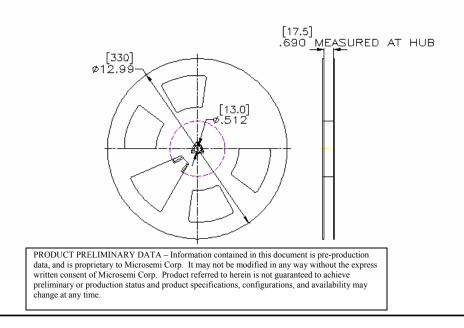
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16 mm TAPE



13 INCH REEL



Microsemi



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Max

4.09

6.61

1.14

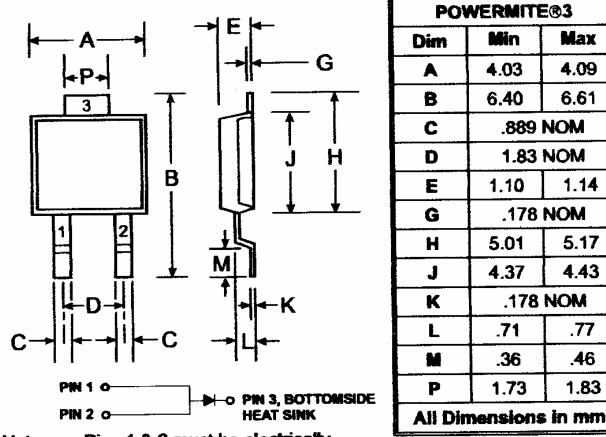
5.17

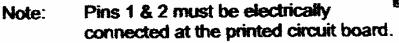
4.43

.77

.46

1.83

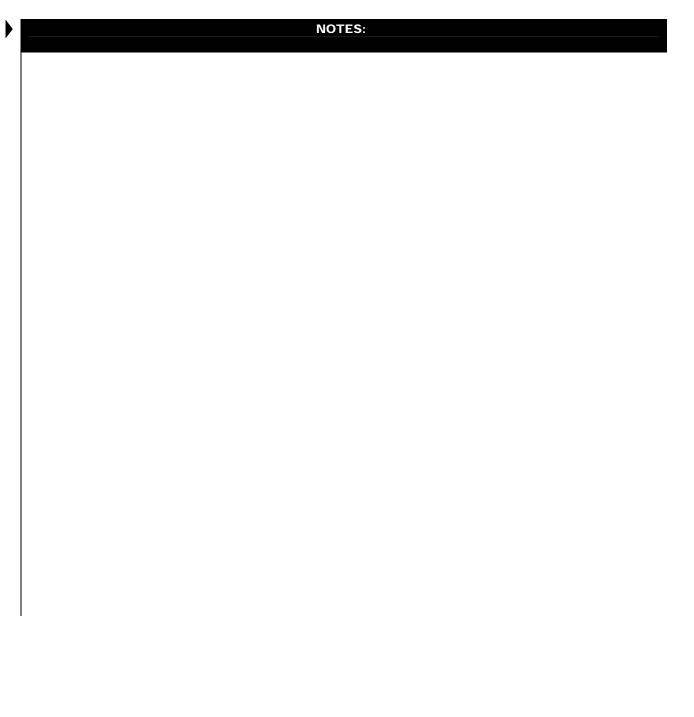




MECHANICAL



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NOTES

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip: UPS340/TR13